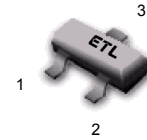
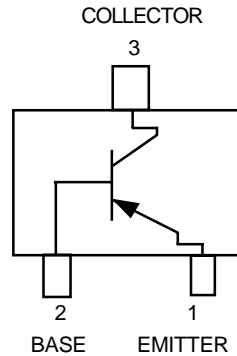


PNP RF Amplifier Transistor

Surface Mount

MSA1022-CT1

CASE 318D-03, STYLE1
SC-59
MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-30	Vdc
Collector-Emitter Voltage	V_{CEO}	-20	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-30	mAdc

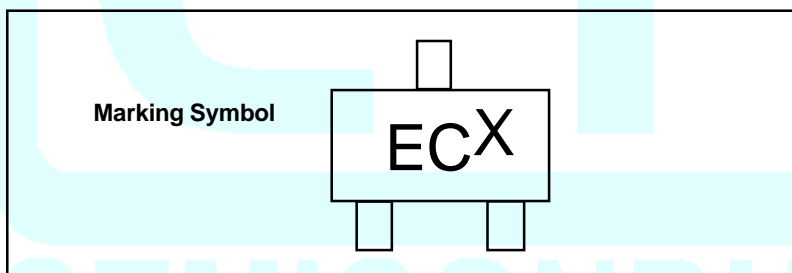
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$)

Characteristic	Symbo	IMin	Max	Unit
Collector Cutoff Current ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	-0.1	μAdc
Collector-Emitter Breakdown Voltage ($V_{CE} = -20\text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	-100	μAdc
Emitter-Base Breakdown Voltage ($V_{EB} = -5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	-10	μAdc
DC Current Gain (1) ($V_{CE} = -10\text{ Vdc}$, $I_C = -1.0\text{ mAdc}$)	h_{FE}	110	220	—
Current-Gain - Bandwidth Product ($V_{CB} = -10\text{ Vdc}$, $I_E = 1.0\text{ mAdc}$)	f_T	150	—	MHz

 1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, D.C. $\leq 2\%$.

DEVICE MARKING


The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.